

**REMARKS**

The Examiner again rejects claims 1, 3, 5 and 8, but this time rejects the claims under 35 USC §103(a) as being unpatentable over Natori et al. in view of Nam further in view of newly cited Yang et al. Yang et al. is cited for its disclosure of a method for manufacturing a ferroelectric memory at paragraph 15 wherein “the required ferroelectric/Iridium structure is disclosed.” This rejection is respectfully traversed.

Paragraph 15 of Yang et al. discloses a structure in which a first conductive layer 21 is made of Ir, IrO<sub>x</sub> or Ir laminated layer, and a ferroelectric layer 22 which is preferably a bi-layered provskite and BLT. A second conductive layer 23 is preferably made of Pt and IrO<sub>x</sub>. Contrary to the assertion of the Examiner, this is not “the required ferroelectric/Iridium structure.”

The required structure of claim 1 includes a ferroelectric layer having an ABO<sub>3</sub> perovskite structure that contains Ir in at least one of an A site and a B site. The cited references do not teach this layer.

For at least the foregoing reasons, the claimed invention distinguishes over the cited art and defines patentable subject matter. Favorable reconsideration is earnestly solicited.

Should the Examiner deem that any further action by applicants would be desirable to place the application in condition for allowance, the Examiner is encouraged to telephone applicants’ undersigned attorney.

Request for Reconsideration  
Serial No.: 10/695,643  
Attorney Docket No. 032057

In the event that this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,

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